



IFW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **SASHIDA, Naoya**

Group Art Unit: **2811**

Serial No.: **10/697,944**

Examiner: **Hoai V. PHAM**

Filed: **October 31, 2003**

P.T.O. Confirmation No.: **8925**

For: **SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING  
THE SAME**

**INFORMATION DISCLOSURE STATEMENT**  
**PURSUANT TO 37 CFR 1.97(b)**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

November 15, 2005

Sir:

The attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached Form PTO-1449. One copy of each of these documents is attached.

No fee or certification is required in connection with this Information Disclosure Statement, since it is being submitted prior to the issuance of a first official action on the merits or expiration of the three month period following the filing date or the entry of the national stage of the above-captioned application.

The above information is presented so that the Patent and Trademark Office can, in the first instance, determine any materiality thereof to the claimed invention. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the documents cited in the attached Form PTO-1449 be made of record therein and appear on the first page of any patent to issue therefrom.



The Commissioner is authorized to charge our Deposit Account No. 01-2340 for any fee which is deemed by the Patent and Trademark Office to be required to effect consideration of this statement.

Respectfully submitted,

ARMSTRONG, KRATZ, QUINTOS,  
HANSON & BROOKS, LLP

Mel R. Quintos  
Attorney for Applicants  
Reg. No. 31,898

MRQ/lrj  
Atty. Docket No. **021557A**  
Suite 1000  
1725 K Street, N.W.  
Washington, D.C. 20006  
(202) 659-2930



**23850**

PATENT TRADEMARK OFFICE

Enclosures: PTO-1449, References (8) and Partial European Search Report dated 10/24/05.



INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. 021557A	Serial No. 10/697,944
	Applicant(s): SASHIDA, Naoya	
	Filing Date: October 31, 2003	Group Art Unit: 2811

### U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
AA	6,121,648	Evans, Jr.	9/19/00	257	295	
AB	6,201,271	Okutoh et al.	3/13/01	257	295	
AC	2002/0021544	Cho et al.	2/21/02	361	200	
AD	6,211,035	Moise et al.	4/3/01	438	396	
AE	2002/0127867	Lee	9/12/02	438	694	

### FOREIGN PATENT DOCUMENTS

	Document No.	Date	Country	Translation (Yes or No)
AF	EP 1 189 262 A2	3/20/02	European	Yes
AG				
AH				

### OTHER DOCUMENTS

AI	SAKODA T. ET AL: "HYDROGEN-ROBUST SUBMICRON IROX/PB (ZR, TI) 03/IR CAPACITORS FOR EMBEDDED FERROELECTRIC MEMORY" JAPANESE JOURNAL OF APPLIED PHYSICS, PUBLICATION OFFICE JAPANESE JOURNAL OF APPLIED PHYSICS. TOKYO, JP, vol. 40, no. 4B, PART 1, April 2001 (2001-04), pages 2911-2916, XPOO1081007 ISSN: 0021-4922 *the whole document*.
AJ	NAKURA T. ET AL: "A hydrogen barrier interlayer dielectric with a SiO <sub>2</sub> /SiON/SiO <sub>2</sub> stacked film for logic-embedded FeRAMs" ELECTRON DEVICES MEETING, 1999. IEDM TECHNICAL DIGEST. INTERNATIONAL WASHINGTON, DC, USA 5-8 DEC. 1999, PISCATAWAY, NJ, USA, IEEE, US, 5 December 1999 (1999-12-05), pages 801-804, XP010372095 ISBN: 0-7803-5410-9 *the whole document*.
AK	Partial European Search Report dated 10/24/05.

Examiner

Date Considered